

POWER SCHOTTKY BARRIER RECTIFIER

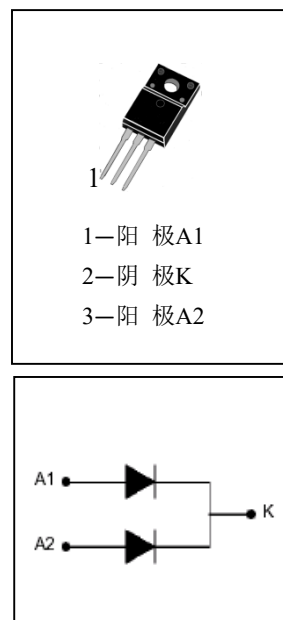
主要用途

低压高频逆变电路，续流电路和保护电路等。

极限值 (Ta=25℃)

T_{stg}	— 贮存温度.....	- 65 ~ 175 °C
T_j	— 结温.....	- 65 ~ 150 °C
V_{RRM}	— 最大反向重复峰值电压.....	100V
V_{RWM}	— 反向峰值工作电压.....	100V
$V_{R(RMS)}$	— 反向工作电压(RMS).....	70 V
V_R	— 最大直流反向电压.....	100 V
$I_{F(AV)}$	— 最大正向平均电流 (Tc=125℃)	整个器件 30A 单个器件 15A
I_{FSM}	— 正向峰值浪涌电流 (单个器件, 60HZ)	200A

外形图及引脚排列



电参数 (Ta=25℃)

参数符号	符 号 说 明	最小值	典型值	最大值	单 位	测 试 条 件
I_R	反向瞬态电流			0.5 100	mA	$V_R = V_{RRM}$, $T_C = 25\text{ °C}$ $T_C = 125\text{ °C}$
V_F	正向瞬态峰值压降 (注 1)			0.84 0.70 0.94 0.82	V	$I_F = 15\text{ A}$, $T_C = 25\text{ °C}$ $I_F = 15\text{ A}$, $T_C = 125\text{ °C}$ $I_F = 30\text{ A}$, $T_C = 25\text{ °C}$ $I_F = 30\text{ A}$, $T_C = 125\text{ °C}$
$R_{th(j-c)}$	结到每只管脚的典型热阻			4.0	°C/W	结到每只管脚
C_j	结电容(注 2)			1000	pF	
dV/dt	电压上升率			10000	V/μs	
V_{ISO}	绝缘电压 (散热板到外表面, t=3 秒)			2000	V	

注 1: 脉冲测试, 脉冲宽度 300μs, 占空比 2%。

注 2: 测试条件 f=1MHz $V_R=4V$ 。

特性曲线

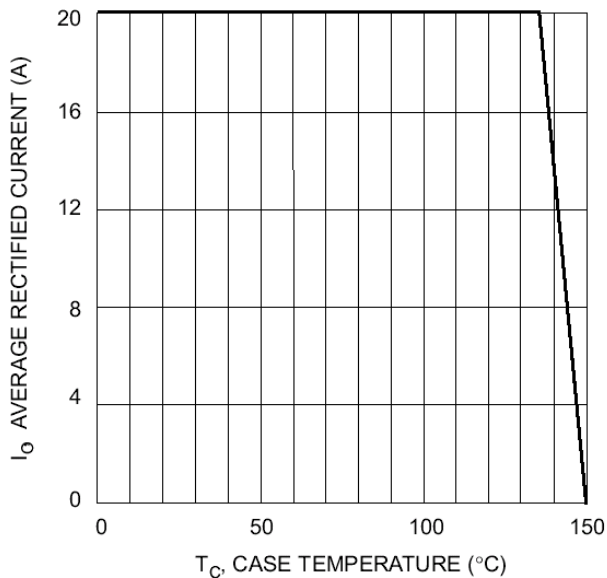


Fig. 1 Fwd Current Derating Curve

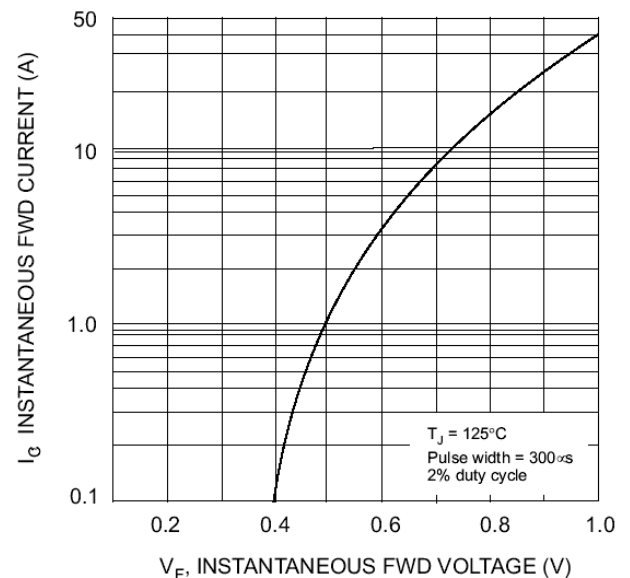


Fig. 2 Typical Forward Characteristics

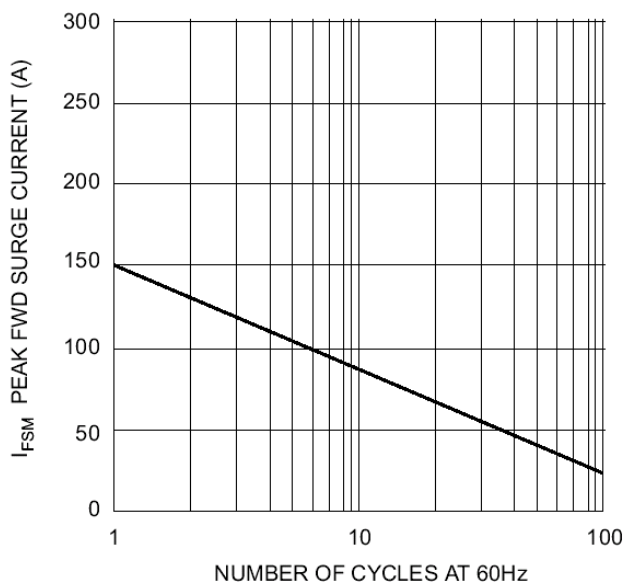


Fig. 3 Max Non-Repetitive Surge Current

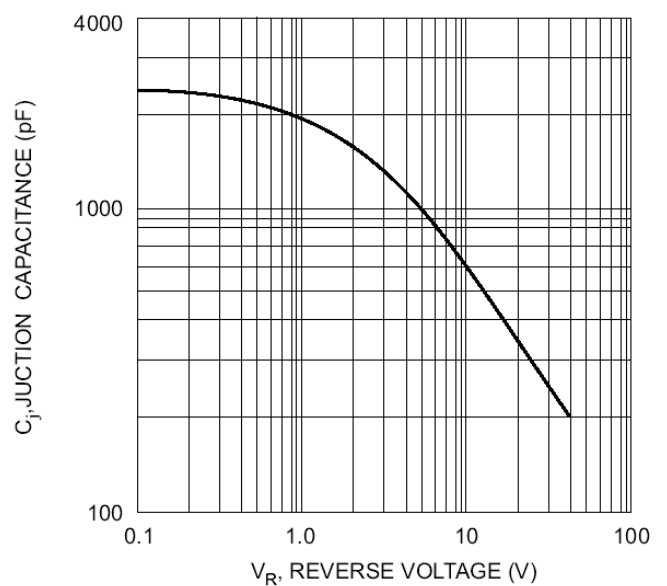


Fig. 4 Typical Junction Capacitance



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MBRF30100CT

NOTE:

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shenzhen Minos reserves the right to make changes in this specification sheet and is subject to change without prior notice.

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